

# MOSFET - Power, Single N-Channel, SUPERFET<sup>®</sup>, FAST, TO247-4L 600 V, 61 mΩ, 41 A

## NTH4LN061N60S5H

### Description

The SUPERFET V MOSFET FAST series helps maximize system efficiency by the extremely low switching losses in hard switching application.

### Features

- 650 V @  $T_J = 150^\circ\text{C}$  / Typ.  $R_{DS(on)} = 48.8\text{ m}\Omega$
- 100% Avalanche Tested
- Pb-Free, Halogen Free / BFR Free and RoHS Compliant

### Applications

- Telecom / Server Power Supplies
- EV Charger / UPS / Solar / Industrial Power Supplies

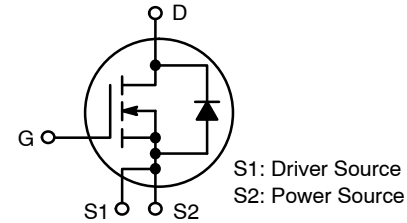
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		$V_{DSS}$	600	V
Gate-to-Source Voltage	DC	$V_{GS}$	$\pm 30$	V
	AC (f > 1 Hz)		$\pm 30$	
Continuous Drain Current	$T_C = 25^{\circ}\text{C}$	$I_D$	41	A
	$T_C = 100^{\circ}\text{C}$		25	
Power Dissipation	$T_C = 25^{\circ}\text{C}$	$P_D$	250	W
Pulsed Drain Current (Note 1)	$T_C = 25^{\circ}\text{C}$	$I_{DM}$	144	A
Pulsed Source Current (Body Diode) (Note 1)		$I_{SM}$	144	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$
Source Current (Body Diode)		$I_S$	41	A
Single Pulse Avalanche Energy	$I_L = 6.7\text{ A}, R_G = 25\text{ }\Omega$	$E_{AS}$	376	mJ
Avalanche Current		$I_{AS}$	6.7	A
Repetitive Avalanche Energy (Note 1)		$E_{AR}$	2.5	mJ
MOSFET dv/dt		dv/dt	120	V/ns
Peak Diode Recovery dv/dt (Note 2)			20	
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)		$T_L$	260	$^{\circ}\text{C}$

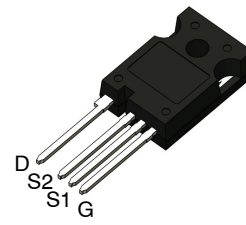
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $I_{SD} \leq 20.5\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 400\text{ V}$ , starting  $T_J = 25^\circ\text{C}$ .

$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	61 mΩ @ 10 V	41 A



N-CHANNEL MOSFET



TO247-4L  
CASE 340CW

### MARKING DIAGRAM



T061N60S5H = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

ZZ = Lot Traceability

### ORDERING INFORMATION

Device	Package	Shipping
NTH4LN061N60S5H	TO247-4L	30 Units / Tube

# NTH4LN061N60S5H

## THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	600	–	–	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$	–	630	–	mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_J = 25^\circ\text{C}$	–	–	2	μA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	–	–	±100	nA

### ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20.5\text{ A}, T_J = 25^\circ\text{C}$	–	48.8	61	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 4.4\text{ mA}, T_J = 25^\circ\text{C}$	2.7	–	4.3	V
Forward Transconductance	$g_{FS}$	$V_{DS} = 20\text{ V}, I_D = 20.5\text{ A}$	–	41.7	–	S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 250\text{ kHz}$	–	4157	–	pF
Output Capacitance	$C_{OSS}$		–	60.1	–	
Time Related Output Capacitance	$C_{OSS(tr)}$	$I_D = \text{Constant}, V_{DS} = 0\text{ to }400\text{ V}, V_{GS} = 0\text{ V}$	–	935	–	
Energy Related Output Capacitance	$C_{OSS(er)}$		–	100	–	
Total Gate Charge	$Q_{G(TOT)}$	$V_{DD} = 400\text{ V}, I_D = 20.5\text{ A}, V_{GS} = 10\text{ V}$	–	74.2	–	nC
Gate-to-Source Charge	$Q_{GS}$		–	20.1	–	
Gate-to-Drain Charge	$Q_{GD}$		–	19.7	–	
Gate Resistance	$R_G$	$f = 1\text{ MHz}$	–	0.7	–	Ω

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 0/10\text{ V}, V_{DD} = 400\text{ V}, I_D = 20.5\text{ A}, R_G = 4.7\text{ }\Omega$	–	31.9	–	ns
Rise Time	$t_r$		–	9.08	–	
Turn-Off Delay Time	$t_{d(OFF)}$		–	82.4	–	
Fall Time	$t_f$		–	2.64	–	

### SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$I_{SD} = 20.5\text{ A}, V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	–	–	1.2	V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, I_{SD} = 20.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 400\text{ V}$	–	416	–	ns
Reverse Recovery Charge	$Q_{RR}$		–	7405	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

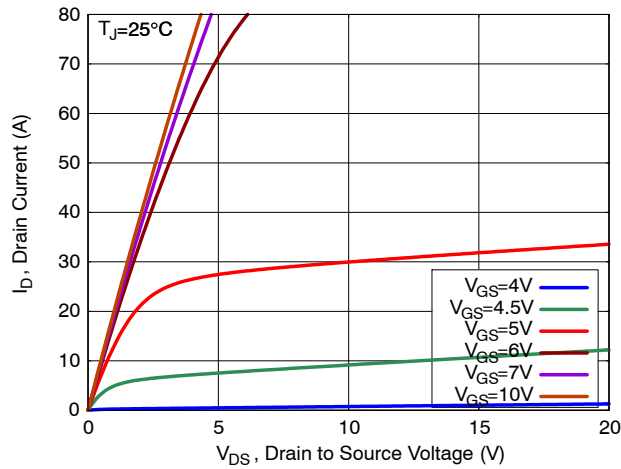


Figure 1. On-Region Characteristics

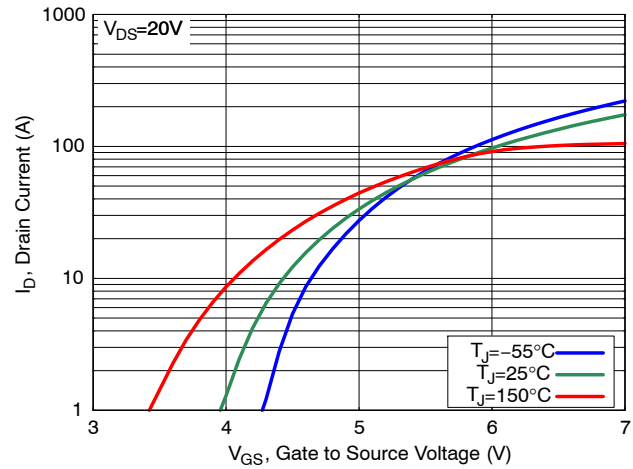


Figure 2. Transfer Characteristics

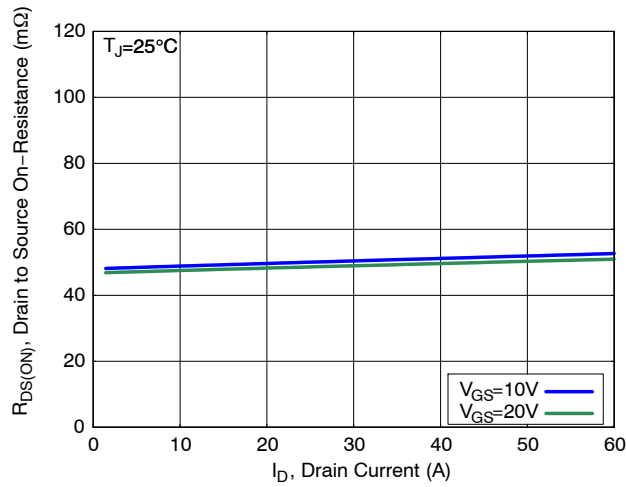


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

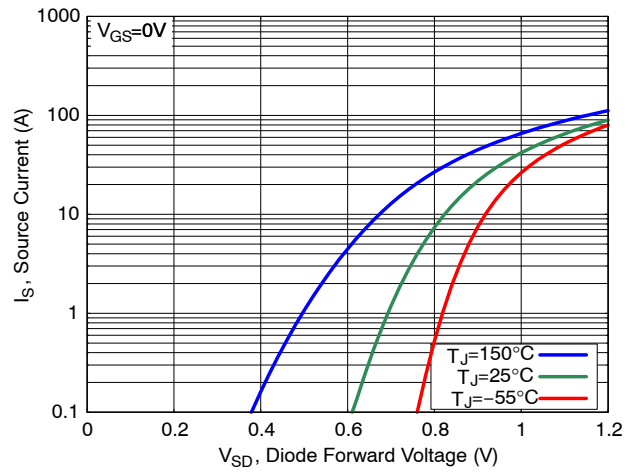


Figure 4. Diode Forward Voltage vs. Source Current

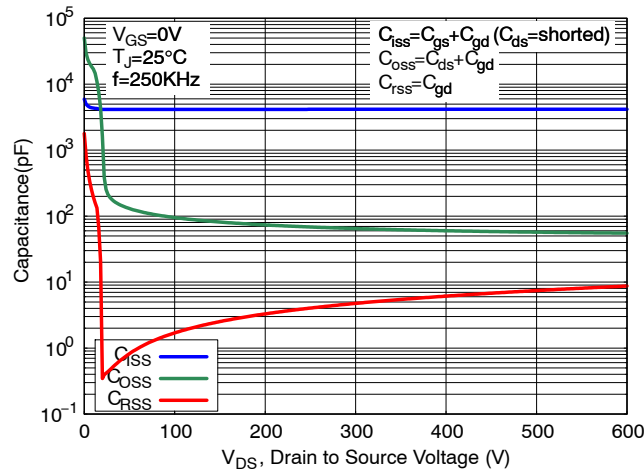


Figure 5. Capacitance Characteristics

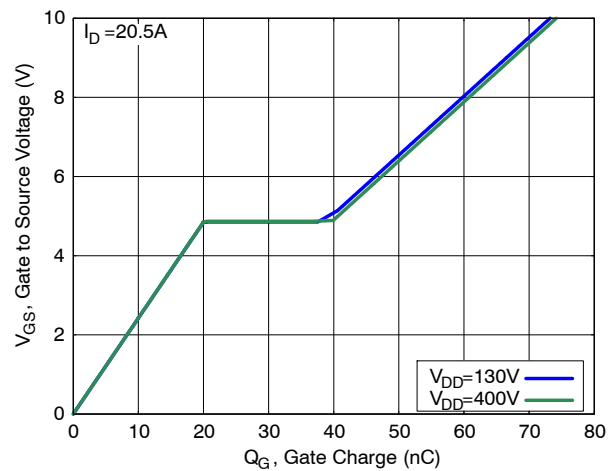


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS

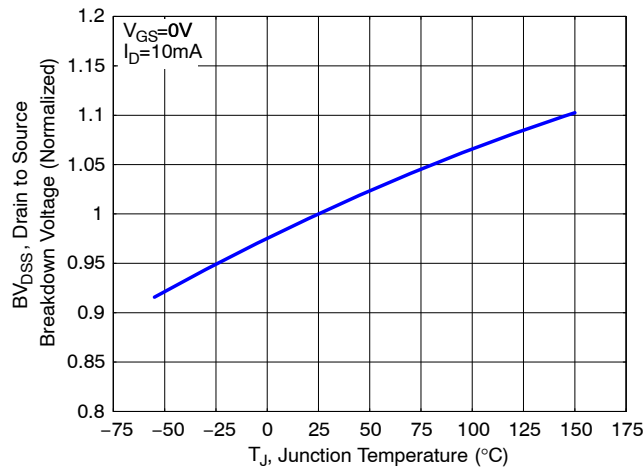


Figure 7. Breakdown Voltage Variation vs. Temperature

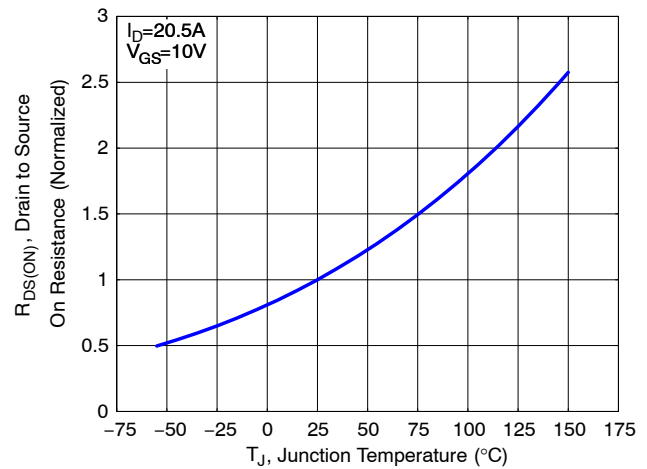


Figure 8. On-Resistance Variation vs. Temperature

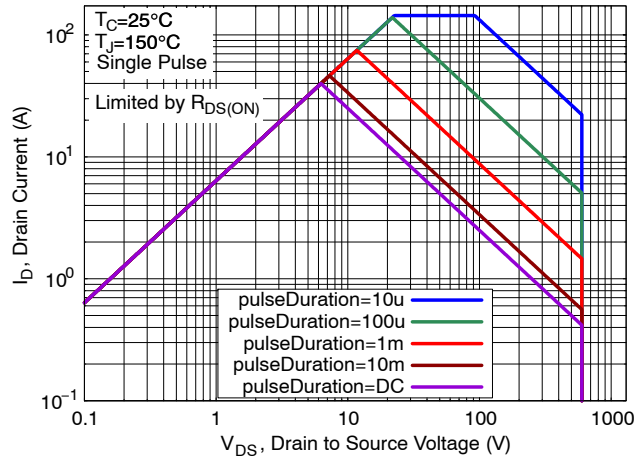


Figure 9. Maximum Safe Operating Area

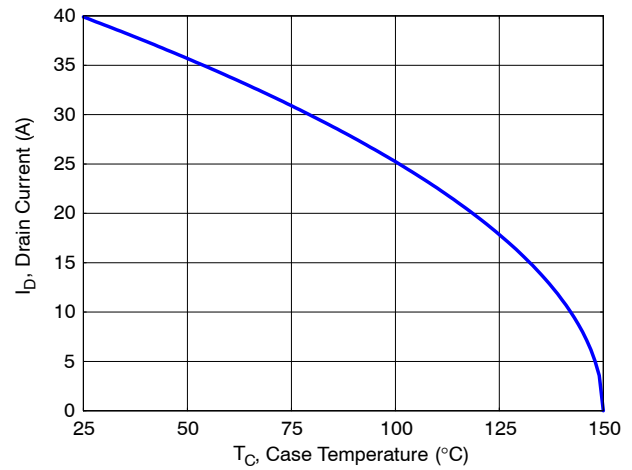


Figure 10. Maximum Drain Current vs. Case Temperature

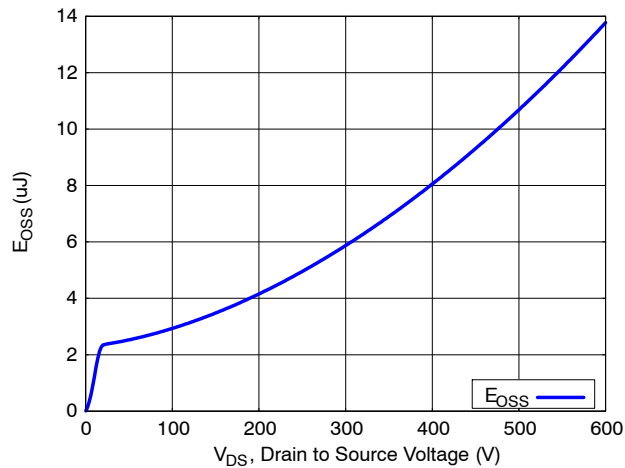


Figure 11. Eoss vs. Drain-to-Source Voltage

# NTH4LN061N60S5H

## TYPICAL CHARACTERISTICS

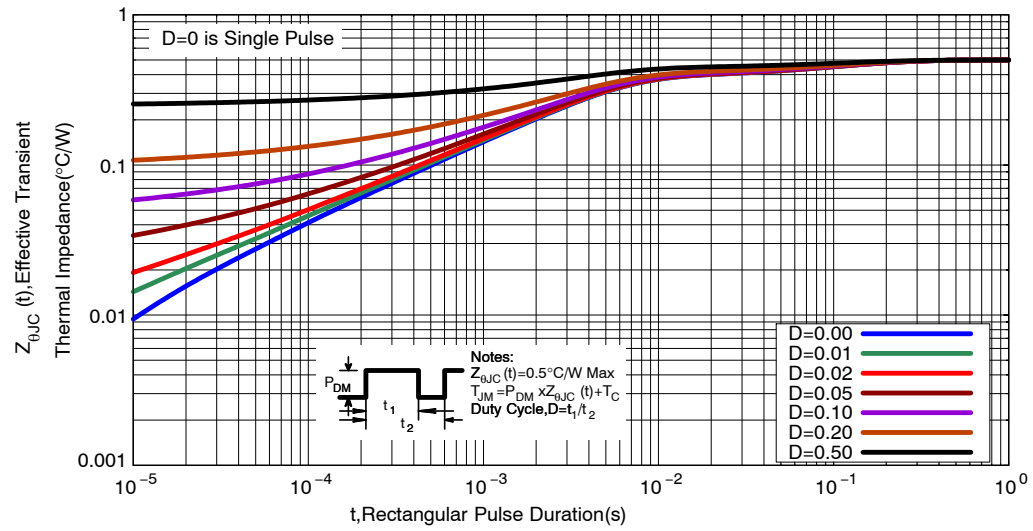
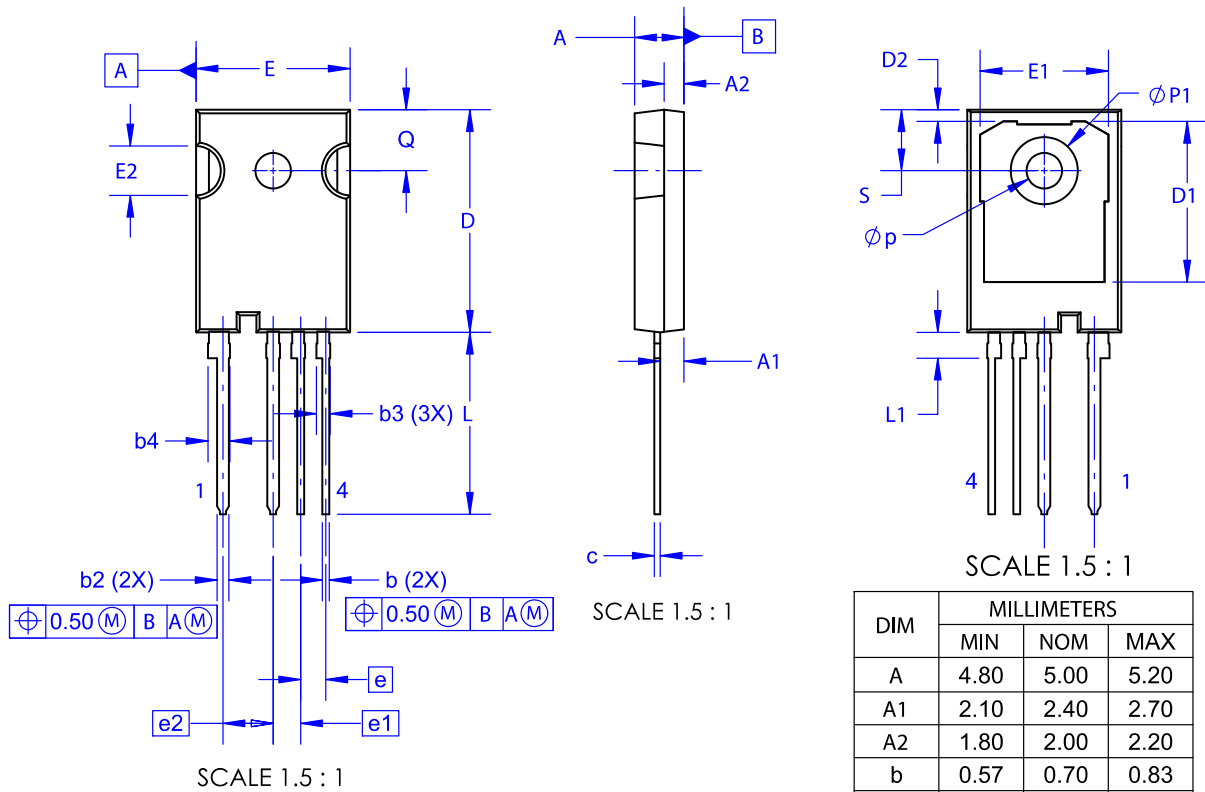


Figure 12. Transient Thermal Impedance

# NTH4LN061N60S5H

## PACKAGE DIMENSIONS

TO-247 4-LEAD, THIN LEADS  
CASE 340CW  
ISSUE A



### NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.

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